

Silicon NPN Power Transistors

2SC2564

DESCRIPTION

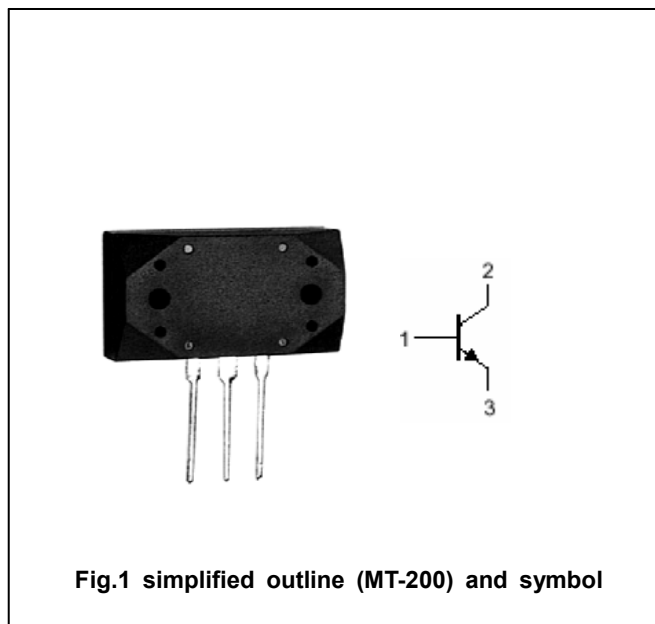
- With MT-200 package
- Complement to type 2SA1094
- High transition frequency

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	140	V
V_{CEO}	Collector-emitter voltage	Open base	140	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		12	A
I_B	Base current		1.2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.1A$; $I_B=0$	140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA$; $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=0.5A$			2.0	V
V_{BE}	Base-emitter on voltage	$I_C=5A$; $V_{CE}=5V$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=140V$; $I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			50	μA
h_{FE-1}	DC current gain	$I_C=1A$; $V_{CE}=5V$	55		240	
h_{FE-2}	DC current gain	$I_C=5A$; $V_{CE}=5V$	40			
f_T	Transition frequency	$I_C=1A$; $V_{CE}=10V$		80		MHz

◆ h_{FE-1} classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

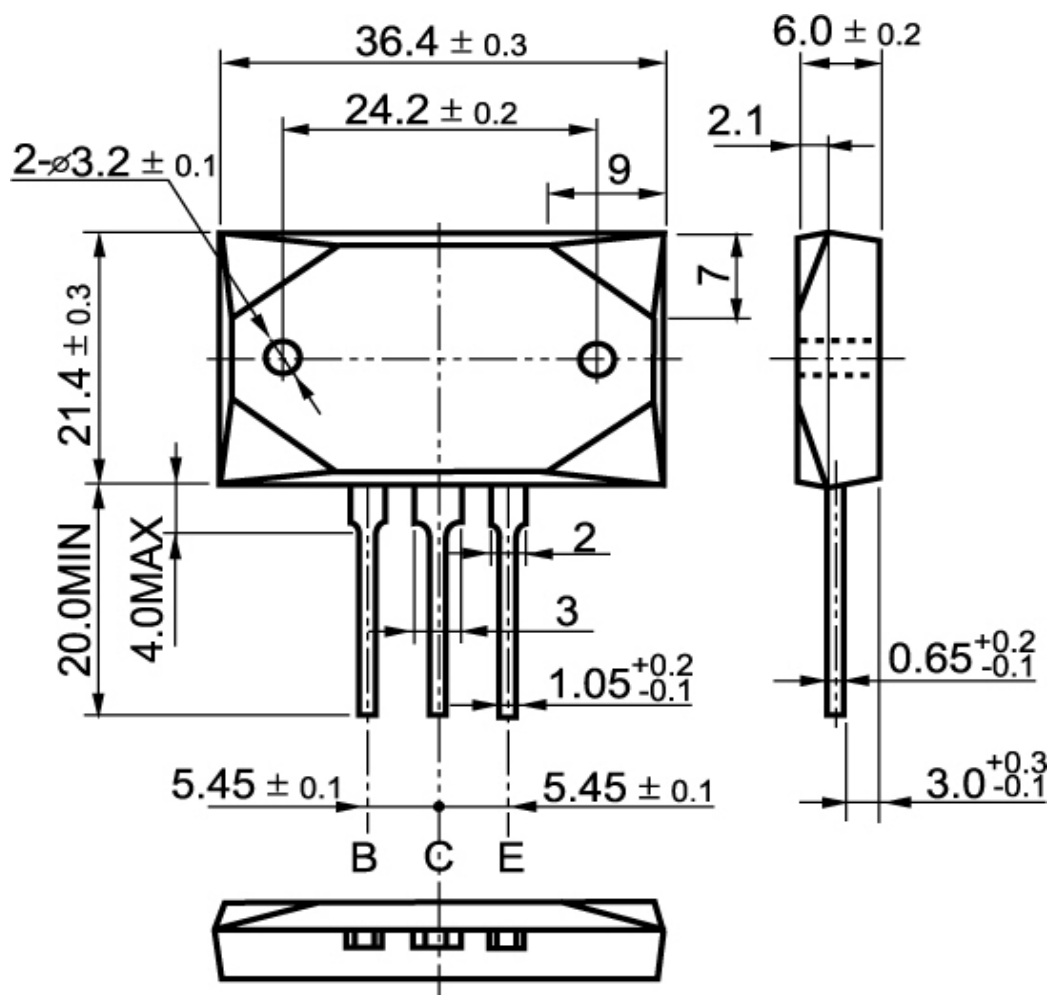


Fig.2 Outline dimensions